

N-channel 40 V, 5 mΩ, logic level MOSFET in LFPAK33 using NextPower-S3 technology

27 April 2020

**Product data sheet** 

#### 1. General description

85 A, logic level N-channel enhancement mode MOSFET in 175 °C LFPAK33 package using advanced TrenchMOS Superjunction technology. This product has been designed and qualified for high efficiency applications at high switching frequencies.

#### 2. Features and benefits

- Avalanche rated, 100% tested
- NextPower-S3 technology delivers 'superfast switching with soft body-diode recovery'
- · Low Q<sub>RR</sub>, Q<sub>G</sub> and Q<sub>GD</sub> for high system efficiency, especially at high switching frequencies
- · Low spiking and ringing for low EMI designs
- High reliability clip bonded and solder die attach Mini Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Exposed leads can be wave soldered, visual solder joint inspection and high quality solder joints
- Low parasitic inductance and resistance

### 3. Applications

- Secondary side synchronous rectification
- DC-to-DC converters
- Brushless DC motor drive
- LED lighting

### 4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	85	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	83	W
Tj	junction temperature			-55	-	175	°C
Static charac	teristics		I				
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; Fig. 10		-	3.9	5	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; Fig. 10		-	4.9	6.4	mΩ
Dynamic cha	racteristics						
Q <sub>GD</sub>	gate-drain charge	$I_D$ = 20 A; $V_{DS}$ = 20 V; $V_{GS}$ = 4.5 V;		0.9	2.9	5.9	nC
Q <sub>G(tot)</sub>	total gate charge	Fig. 12; Fig. 13		8.5	13	18	nC

[1] 85A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

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## 5. Pinning information

Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	S	source		D			
2	S	source					
3	S	source		G-UH			
4	G	gate		mbb076 S			
mb	D	Mounting base; connected to drain	LFPAK33 (SOT1210)				

## 6. Ordering information

Table 3. Ordering information							
Type number	Package	cage					
	Name	Description	Version				
PSMN5R0-40MLH	LFPAK33	Plastic, single ended surface mounted package (LFPAK33); 8 leads; 0.65 mm pitch	SOT1210				

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PSMN5R0-40MLH	5H0L40

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

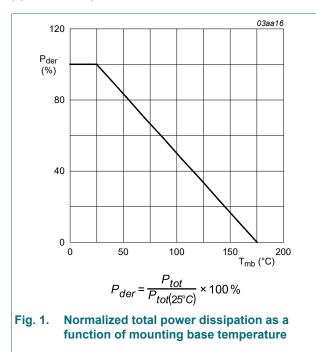
Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>DSM</sub>	peak drain-source voltage	$t_p \le 20 \text{ ns}; f \le 500 \text{ kHz}; E_{DS(AL)} \le 200 \text{ nJ};$ pulsed		-	45	V
V <sub>DGR</sub>	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	40	V
V <sub>GS</sub>	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	83	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	85	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	62	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	349	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-draii	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	85	А

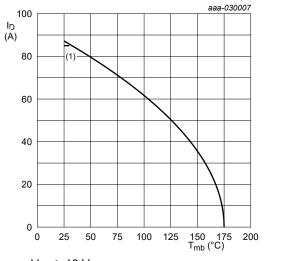
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Symbol	Parameter	Conditions		Min	Max	Unit
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>mb</sub> = 25 °C		-	349	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	source avalanche energy	$ \begin{split} &I_D = 29.6 \text{ A};  \text{V}_{\text{sup}} \leq \text{ 40 V};  \text{R}_{\text{GS}} = 50  \Omega; \\ &\text{V}_{\text{GS}} = 10 \text{ V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped}; \\ &t_p = 107  \mu\text{s} \end{split} $	[2]	-	82.7	mJ
		$ \begin{array}{l} I_{D} = 20 \text{ A};  V_{sup} \leq \ 40 \text{ V};  R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \text{ V};  T_{j(init)} = 25 \ ^{\circ}\text{C};  unclamped; \\ t_{p} = 245 \ \mu s \end{array} $	[2]	-	127.6	mJ
I <sub>AS</sub>	non-repetitive avalanche current		[2]	-	70	A

[1] 85A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Protected by 100% test

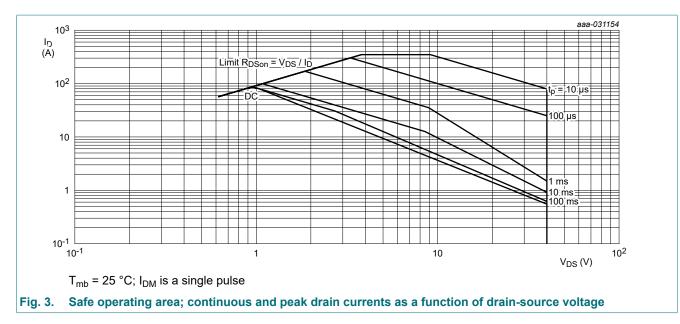




V<sub>GS</sub> ≥ 10 V

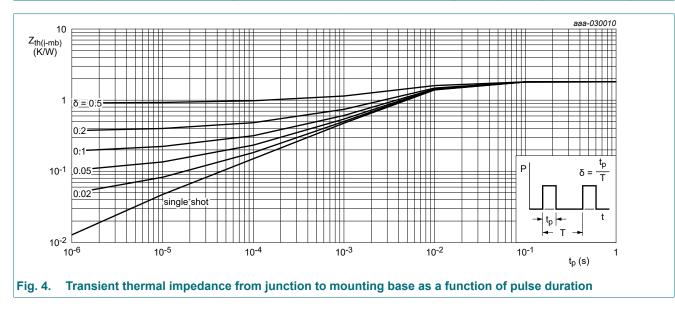
(1) 85A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature



#### 9. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	1.61	1.81	K/W
R <sub>th(j-a)</sub>	thermal resistance from F	Fig. 5	-	50	-	K/W
junction to ambient	Fig. 6	-	130	-	K/W	

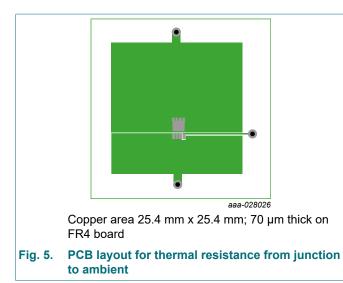


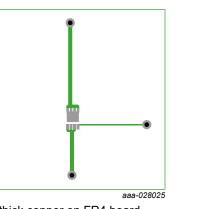
#### PSMN5R0-40MLH

#### Nexperia

# PSMN5R0-40MLH

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70 µm thick copper on FR4 board

Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient

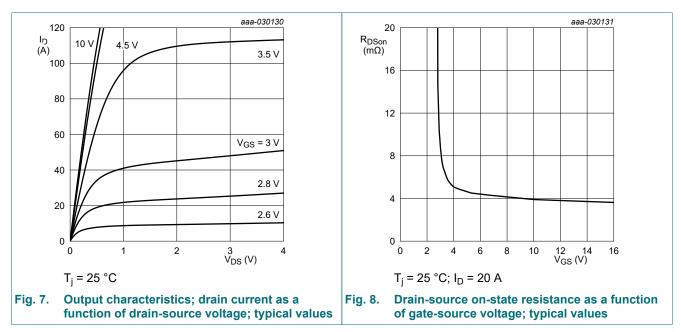
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	-	-	V
	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C	1.45	1.77	2.15	V
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-4.3	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.04	1	μA
		V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	0.9	-	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; Fig. 10	-	3.9	5	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 175 °C; <u>Fig. 11</u>	-	-	10.9	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 25 °C; Fig. 10	-	4.9	6.4	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 20 A; T <sub>j</sub> = 175 °C; Fig. 11	-	-	14	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.3	0.8	2	Ω
Dynamic cha	racteristics	·				
Q <sub>G(tot)</sub>	total gate charge	$I_{D} = 20 \text{ A}; V_{DS} = 20 \text{ V}; V_{GS} = 4.5 \text{ V};$ Fig. 12; Fig. 13	8.5	13	18	nC
		$I_D$ = 20 A; $V_{DS}$ = 20 V; $V_{GS}$ = 10 V; Fig. 12; Fig. 13	18	28	39	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V	-	15	-	nC

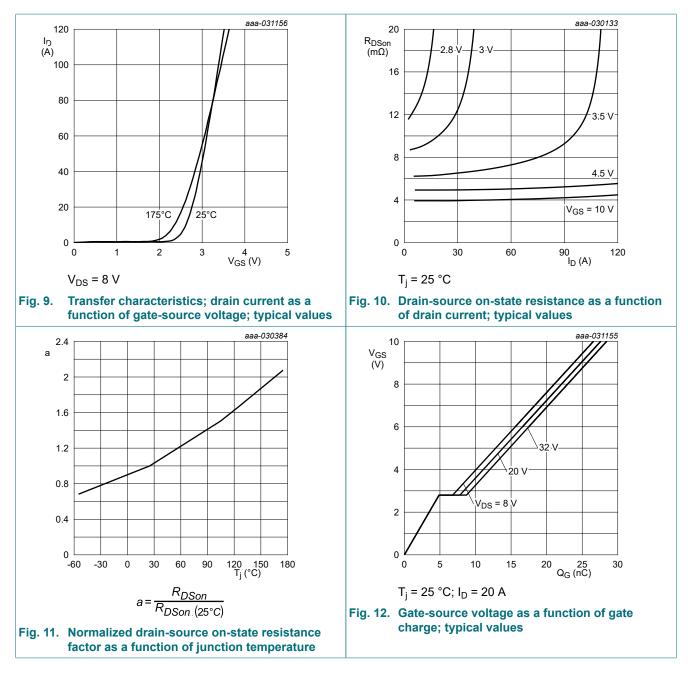
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q <sub>GS</sub>	gate-source charge	$I_D$ = 20 A; $V_{DS}$ = 20 V; $V_{GS}$ = 4.5 V;		3	4.9	7.4	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	Fig. 12; Fig. 13		1.7	2.9	4.3	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge			1.2	2	2.8	nC
Q <sub>GD</sub>	gate-drain charge			0.9	2.9	5.9	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 20 A; V <sub>DS</sub> = 20 V; <u>Fig. 12; Fig. 13</u>		-	2.8	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 20 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		1230	1892	2649	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>		318	490	686	pF
C <sub>rss</sub>	reverse transfer capacitance			20	68	150	pF
t <sub>d(on)</sub>	turn-on delay time			-	18	-	ns
t <sub>r</sub>	rise time			-	22	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	17	-	ns
t <sub>f</sub>	fall time	-		-	12	-	ns
Q <sub>oss</sub>	output charge	$V_{GS}$ = 0 V; $V_{DS}$ = 20 V; f = 1 MHz; T <sub>j</sub> = 25 °C		-	15	-	nC
Source-drai	in diode			·			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 20 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <u>Fig. 15</u>		-	0.82	1	V
t <sub>rr</sub>	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$		-	24	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 20 V; <u>Fig. 16</u>	[1]	-	18	-	nC
t <sub>a</sub>	reverse recovery rise time			-	15	-	ns
t <sub>b</sub>	reverse recovery fall time			-	10	-	ns

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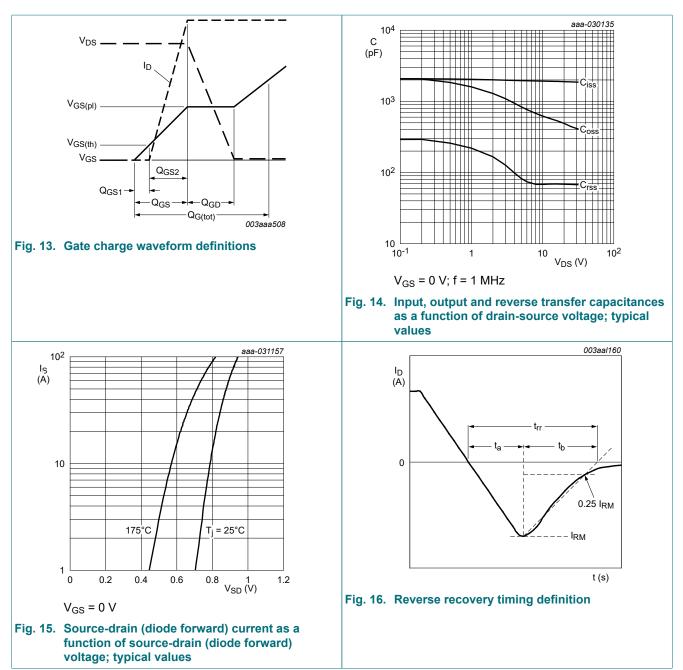
[1] includes capacitive recovery



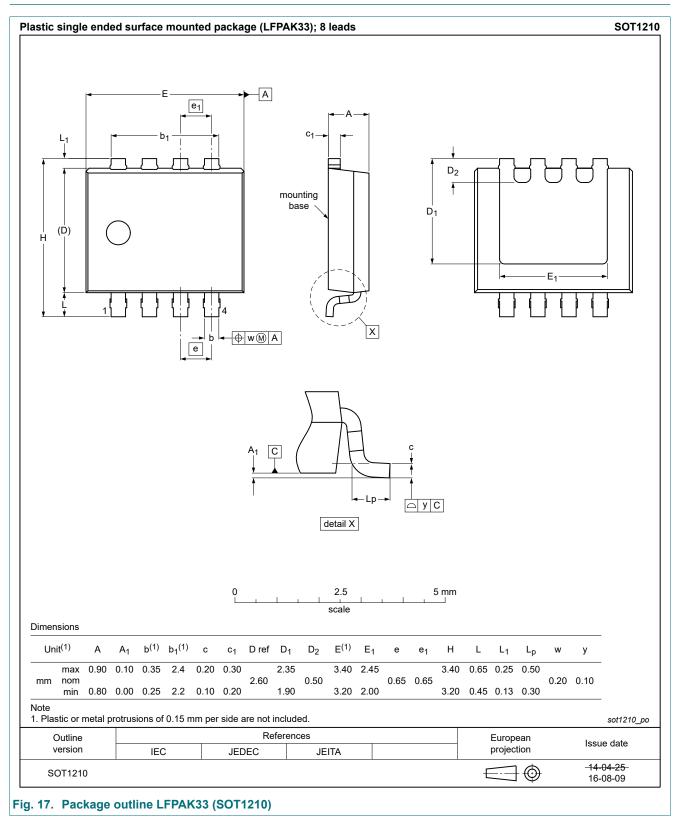
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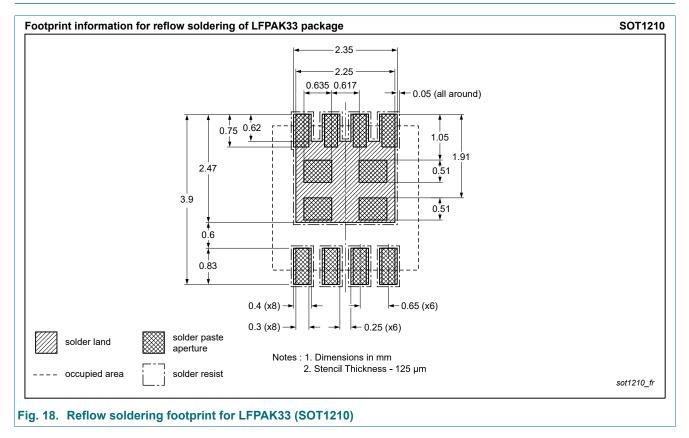
#### N-channel 40 V, 5 mΩ, logic level MOSFET in LFPAK33 using NextPower-S3 technology



### 11. Package outline



### 12. Soldering



PSMN5R0-40MLH

### 13. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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